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XA-9630

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Tsuyoshi FUJIWARA et al.

Appln. No.: 10/083,416

Group Art Unit: 2813

Filed: February 27, 2002

Examiner: Thang Nguyen

For: METHOD OF MANUFACTURING SEMICONDUCTOR INTEGRATED

CIRCUIT DEVICE COMPRISING A MEMORY CELL AND A

CAPACITOR

AMENDMENT

Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

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In response to the Office Action mailed August 20, 2003, 2003, please amend the above-identified patent application as indicated below.

Amendments to the claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 12 of this paper.

high-density plasma CVD. The rejection proposes to cure this deficiency of Tsai by reliance upon Basceri et al.

However, as pointed out in the foregoing comments, there is no teaching or suggestion in Basceri et al. (or in Tsai) of using high-density plasma CVD in an environment such as that recited in Applicants' claims. In other words, there is no suggestion in the prior art of combining the teachings of the references in any manner that could reasonably be expected to produce the inventions recited in Applicants' claims.

Accordingly, it is respectfully submitted that all of the claims now presented should be allowed and that this application should be passed to issue.

The Commissioner is hereby authorized to charge to

D posit Account No. 50-1165 any fees under 37 C.F.R. §§

1.16 and 1.17 that may be required by this paper and to

credit any overpayment to that Account. If any extension

of time is required in connection with the filing of this

paper and has not been requested separately, such extension is hereby requested.

Respectfully submitted,

Nelson H. Shapiro Reg. No. 17,095

NHS:1mb:jb

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November 20, 2003